

# Contents

<b>1</b>	<b>Introduction</b>	<b>1</b>
1.1	Motivation . . . . .	3
1.2	Outline . . . . .	5
<b>2</b>	<b>Theoretical Background</b>	<b>7</b>
2.1	Organic Semiconductors . . . . .	7
2.2	Theory of Charge Transport in Disordered Organic Semiconductors . . . . .	8
2.3	Doping of Organic Semiconductors . . . . .	11
2.3.1	Integer Charge Transfer Model . . . . .	11
2.3.2	Intermolecular Orbital Hybridization . . . . .	13
2.3.3	Internal Interface Charge Transfer Doping Model . . . . .	15
2.3.4	Influence of Doping on Mobility . . . . .	16
2.4	IV Characteristics . . . . .	17
2.5	Charge Injection at Contacts . . . . .	19
2.5.1	MoO <sub>3</sub> Injection Layers . . . . .	19
2.5.2	LiF Injection Layers . . . . .	20
2.6	OLED Theory . . . . .	21
2.6.1	Working Principle of OLEDs . . . . .	21
2.6.2	OLED Stack Employed in this Work . . . . .	23
<b>3</b>	<b>Experimental Details</b>	<b>25</b>
3.1	The Clustertool: An Integrated UHV System . . . . .	25
3.2	Analytical Methods . . . . .	28
3.2.1	Transmission Electron Microscopy . . . . .	28
3.2.1.1	TEM Spectroscopy . . . . .	29
3.2.1.2	Electron Tomography . . . . .	33
3.2.1.3	Microscopes . . . . .	34

3.2.2	Probing Electronic Properties . . . . .	35
3.2.2.1	Photoelectron Spectroscopy . . . . .	35
3.2.2.2	FTIR Spectroscopy . . . . .	37
3.2.3	Electrical Measurements . . . . .	38
3.2.3.1	IV and Cryo-IV Measurements . . . . .	38
3.2.3.2	OLEDs . . . . .	39
3.3	Sample Preparation . . . . .	39
3.3.1	Thin Film Growth . . . . .	39
3.3.2	Materials . . . . .	41
3.3.2.1	CBP . . . . .	41
3.3.2.2	MoO <sub>3</sub> . . . . .	42
3.3.3	Preparation of TEM Samples . . . . .	42
3.3.4	Device Fabrication . . . . .	44
3.3.4.1	Hole-Only Devices . . . . .	45
3.3.4.2	OLEDs . . . . .	49
<b>4</b>	<b>MoO<sub>3</sub>-Doped CBP Thin Films</b>	<b>51</b>
4.1	Structural Investigations . . . . .	51
4.1.1	Bright-Field TEM . . . . .	51
4.1.2	TEM Spectroscopy . . . . .	54
4.1.2.1	ESI in the Core Loss Regime . . . . .	55
4.1.2.2	ESI in the Low Loss Regime . . . . .	57
4.1.3	Electron Tomography . . . . .	60
4.1.4	Influence of the Substrate Temperature . . . . .	71
4.1.5	Discussion of Filament Diameter . . . . .	78
4.1.6	Description of MoO <sub>3</sub> Filament Growth . . . . .	80
4.2	Electronic Properties . . . . .	85
4.2.1	The CBP/MoO <sub>3</sub> Interface . . . . .	85
4.2.2	Electronic Investigations of Doped Films . . . . .	86
4.2.2.1	Influence of Charge Transfer on Electronic Properties .	87
4.2.2.2	Doping Efficiency . . . . .	91
4.3	Electrical Measurements . . . . .	93
4.3.1	Probing the Electrical Anisotropy . . . . .	93

4.3.2	Determination of Activation Energies from Temperature-Dependent IV Measurements . . . . .	97
4.3.3	Influence of Substrate Temperature on Electrical Properties . . . . .	101
4.4	Doping Model Based on Structural, Electronic and Electrical Findings . .	102
4.4.1	Factors Influencing the Doping Efficiency . . . . .	102
4.4.2	Description of Charge Transport in MoO <sub>3</sub> -Doped CBP Layers . . .	104
<b>5</b>	<b>Angle Dependence of LiF/TPBi Interface</b>	<b>111</b>
5.1	Performance of OLEDs with Different Deposition Angles . . . . .	111
5.2	Investigation of the TPBi/LiF Interface using XPS . . . . .	116
<b>6</b>	<b>Conclusion</b>	<b>121</b>
6.1	Summary . . . . .	121
6.2	Outlook . . . . .	123
<b>A</b>	<b>Molecular Structures</b>	<b>127</b>
<b>B</b>	<b>Journal Publications and Conference Presentations</b>	<b>129</b>
<b>Bibliography</b>		<b>133</b>